

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

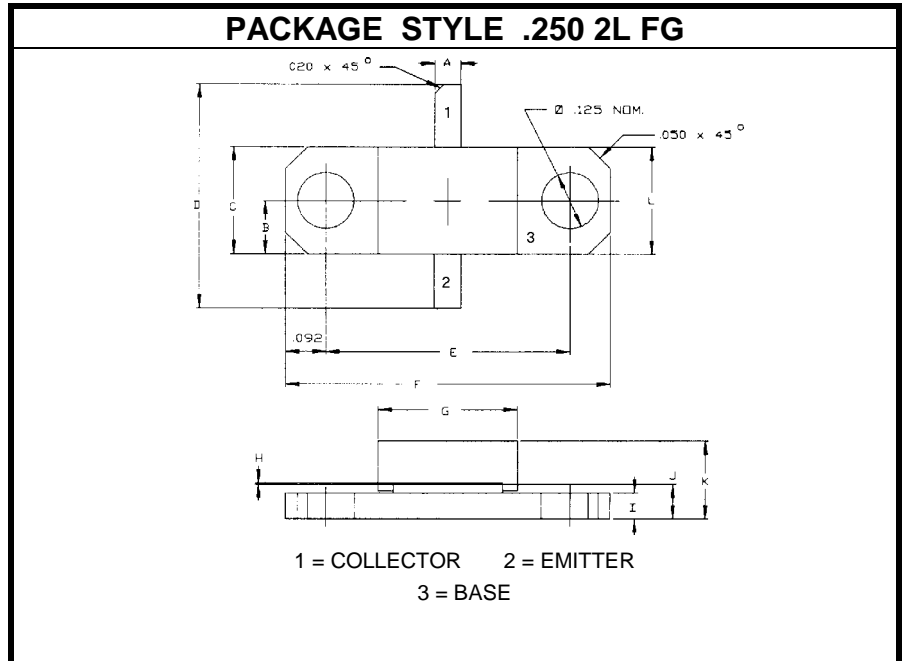
The **ASI SD1899** is a Common Base Device Designed for class C Applications.

FEATURES INCLUDE:

- Gold Metalization
- Input/Output Matching
- Diffused Ballast Resistors

MAXIMUM RATINGS

I_C	3.8 A
V_{CB0}	50 V
V_{CEO}	25 V
P_{DISS}	66 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	6.5 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 25 mA	50			V
BV_{EBO}	I _E = 10 mA	3.5			V
I_{CEO}	V _{CE} = 25 V			25	mA
h_{FE}	V _{CE} = 8.0 V I _C = 400 mA	20	60	100	---
C_{OB}	f = 1.0 MHz		24		pF
P_G η_C	V _{CC} = 28 V P _{out} = 30 W f = 1.6 – 1.7 GHz	7.0	40	8.2	dB %